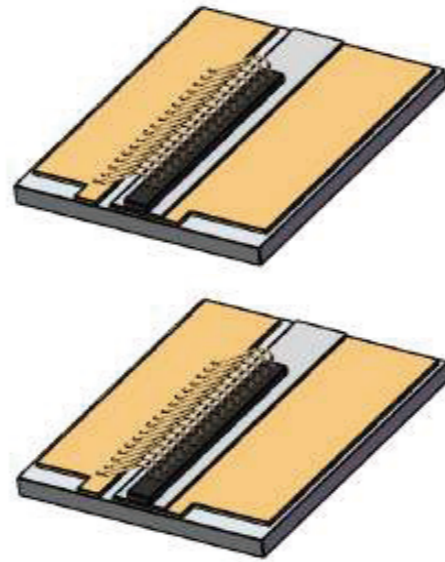


# COS Encapsulated Diode Laser

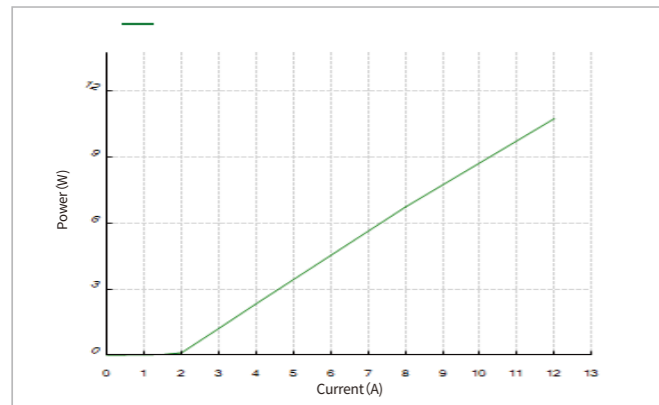
## Product Description

COS encapsulated semiconductor laser

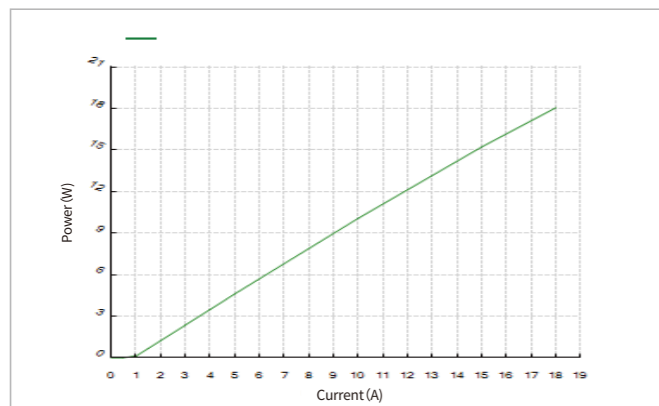
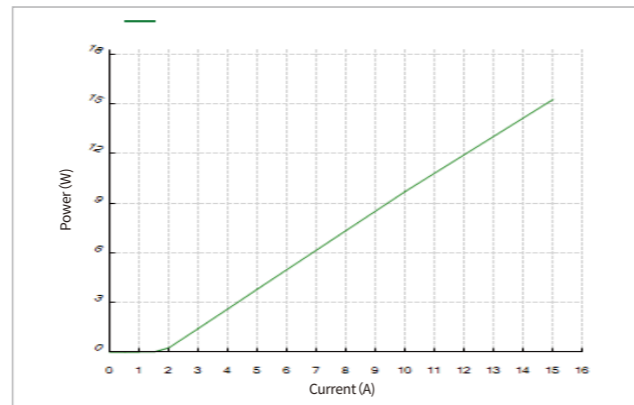


## Application Advantages

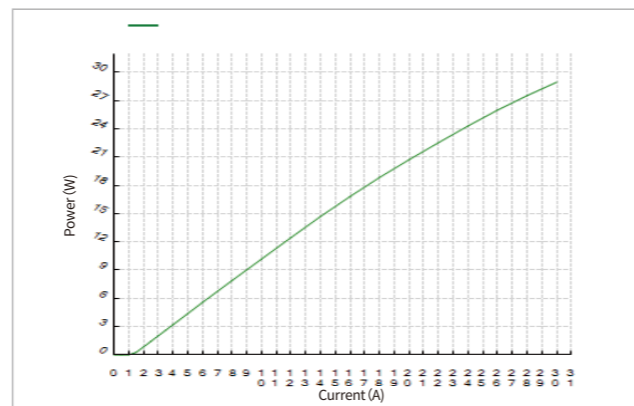
- 230μm luminous surface width
- High polarization states can be used to polarize the beam
- High stability, high reliability



808-10W/880-15W Power curve



915-19W/976-30W Power curve



## Specifications

Parameter	Unit	Parameter			
Product Model		808	880	915	976
Output Power	W	8~10	10~15	12~35	
Central Emission Wavelength	nm	808	878	915	976
Threshold Current	A	1~1.8	1.5	0.6~1.8	
Operating Current	A	8.5~11	11~15	12~35	
Operating Voltage	V	1.75			
Vertical Far Field 95% PIB [Deg]	°	58			
Lateral Far Field 95% PIB [Deg]	°	11			
Slope Efficiency		1.1		1.03	
Conversion Efficiency	%	52~54	52~57	55~57	
Wavelength Center (I=2A)		800~804	874~877	903~915	960~970
Spectral Width (FWHM)	nm	6			
Polarisation Ratio TE / (TM+TE)	%	80		95	
Emitter Width	μm	200~400		96~230	100~230
Welding Temperature	°C	≤260			
Operating Temp.	°C	15~40			
Storage Temp.	°C	0~70			
Wavelength Temperature Coefficient	nm/°C	0.3			
Dimension	mm	4.8×4.05×0.456 / 4.5×5.7×0.5			
Weight	g	<1			

· Customizable products allow flexible configuration of model parameters according to specific needs.